

File View Edit Tools Window Help

☐ Pending  
☒ Active  
☐ Failed  
☐ Saved

L1: 168974781 peripher\$2 logic edge border perimeter support\$4 driver  
 L2: 138835531 (memory cell array core)  
 L3: 15888131 (F01 field adj) extide ST1 (Isolatt\$3 (element adj) (insulat\$4 sep  
 L4: 150334611 (open\$5 trench groove)  
 L5: 144628531 deeper lower  
 L6: 1228311 L4 adj L3  
 L7: 153462251 L3 L4  
 L8: 18383261 L7 near\$ L1  
 L9: 12811621 L7 near\$ L2  
 L10: 1176121 L8 with L9  
 L11: 111771 L10 with L5  
 L12: 18286791 etch\$4 resist  
 L13: 12441 L11 and L12  
 L14: 1761 L13 and L6  
 L15: 1201 Backward citation search 1  
 L16: 1101 Backward citation search 2  
 L17: 171 Backward citation search 3  
 L18: 11081 L14 L15 L16 L17

S2: 11 09/948877  
 S3: 117361 "KOMBIKLUXE PHILIPS".as  
 S1: 10110/753914  
 S4: 111 01/200418

L14 L15 L16 L17  
 May 2005

	U	Inventor	Document	Issu	P	Title	Current	Current I	Retrieval	S	C	P	Image	Def
1	<input checked="" type="checkbox"/>	Kumikyo, T	US 6762477	2004	4	Semiconductor device	257/50	257/398		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 676247
2	<input checked="" type="checkbox"/>	Saito, Kenji	US 659660	2003	9	Method of manufacturing non-volatile	438/42	257/E21.6		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 659660
3	<input checked="" type="checkbox"/>	Maeda, Shi	US 6314021	2001	4	Nonvolatile semiconductor memory de	365/18	257/314		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 631402
4	<input checked="" type="checkbox"/>	Haskett, Joe	US 449562	1985	11	Process for forming grooves having dif	438/42	257/510		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 449502
5	<input checked="" type="checkbox"/>	Kim, Sun-Yo	US 2004018	2004	18	Self-aligned trench isolation method a	257/37			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200401
6	<input checked="" type="checkbox"/>	Yu, Hau-She	US 200500	2005	18	Methods of simultaneously fabricating	438/78			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20050
7	<input checked="" type="checkbox"/>	Han, Chang	US 200500	2005	10	Method for fabricating semiconductor	438/25	438/275		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20050
8	<input checked="" type="checkbox"/>	Yao, Jiang e	US 200500	2005	12	METHOD OF FORMING SHALLOW TRENCH	438/42			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20050
9	<input checked="" type="checkbox"/>	Kim, Sun-Yo	US 2004021	2004	14	Nonvolatile memory device having STIs	257/81			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040
10	<input checked="" type="checkbox"/>	Tanaka, Yos	US 2004018	2004	91	Semiconductor device comprising cap	438/25	257/E21.6		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200401

Ready

BEST AVAILABLE COPY